

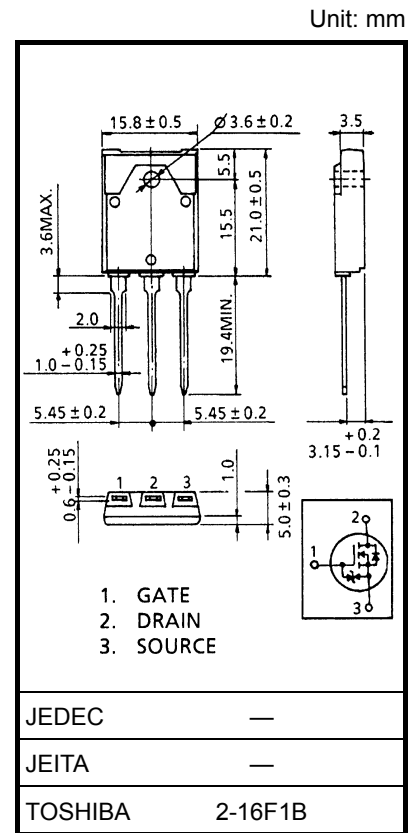
# 2SK3017

DC-DC Converter, Relay Drive and Motor Drive Applications

- Low drain-source ON resistance :  $R_{DS(ON)} = 1.05 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 720 V$ )
- Enhancement mode :  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

| Characteristics                                | Symbol         | Rating         | Unit       |
|--|----------------|----------------|------------|
| Drain-source voltage                           | $V_{DSS}$      | 900            | V          |
| Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )   | $V_{DGR}$      | 900            | V          |
| Gate-source voltage                            | $V_{GSS}$      | $\pm 30$       | V          |
| Drain current                                  | DC (Note 1)    | $I_D$          | 8.5 A      |
|  | Pulse (Note 1) | $I_{DP}$       | 25.5 A     |
| Drain power dissipation ( $T_c = 25^\circ C$ ) | $P_D$          | 90             | W          |
| Single pulse avalanche energy (Note 2)         | $E_{AS}$       | 966            | mJ         |
| Avalanche current                              | $I_{AR}$       | 8.5            | A          |
| Repetitive avalanche energy (Note 3)           | $E_{AR}$       | 9              | mJ         |
| Channel temperature                            | $T_{ch}$       | 150            | $^\circ C$ |
| Storage temperature range                      | $T_{stg}$      | $-55 \sim 150$ | $^\circ C$ |



Weight: 5.8 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

| Characteristics                        | Symbol         | Max  | Unit           |
|--|----------------|------|----------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 1.39 | $^\circ C / W$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 41.6 | $^\circ C / W$ |

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C$  (initial),  $L = 24.5 mH, R_G = 25 \Omega, I_{AR} = 8.5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

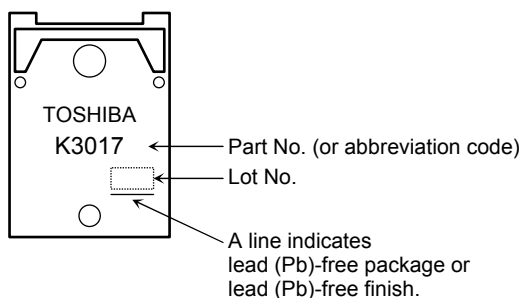
## Electrical Characteristics (Ta = 25°C)

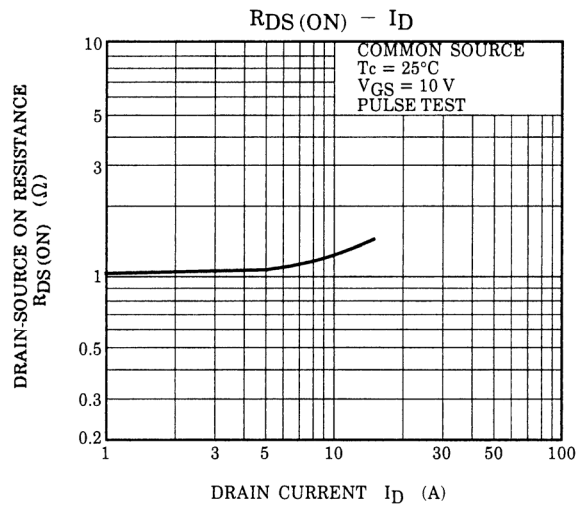
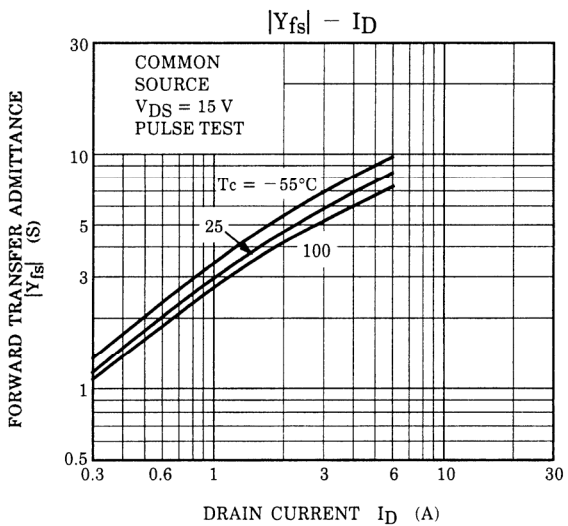
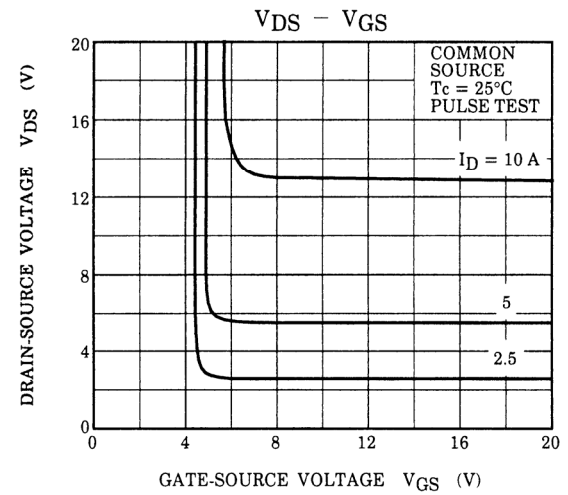
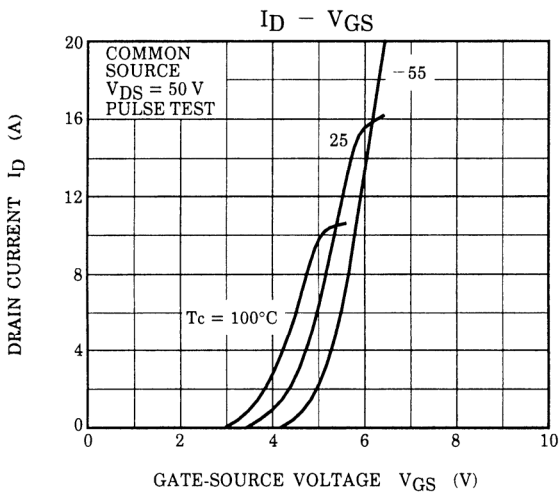
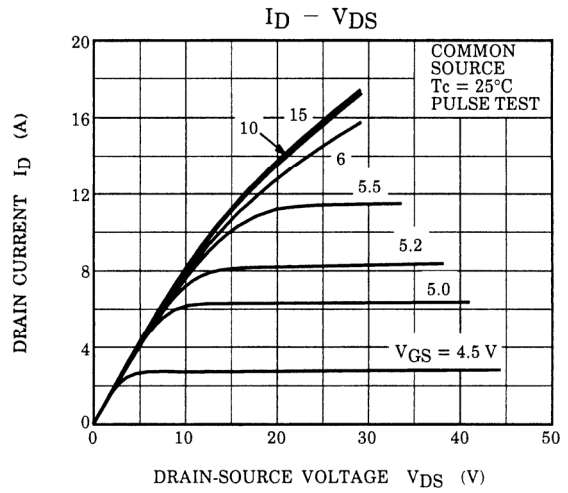
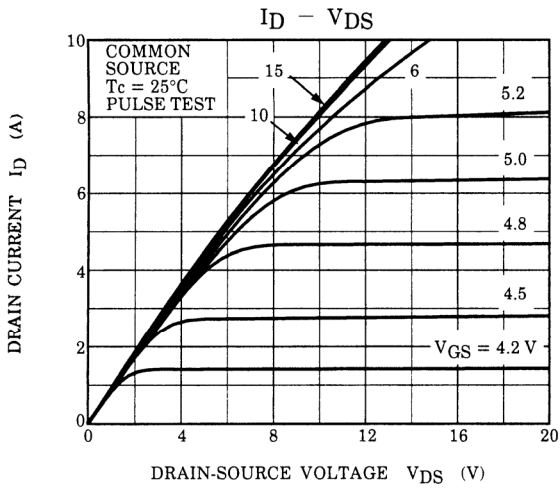
| Characteristics                                 |               | Symbol        | Test Condition  | Min      | Typ. | Max      | Unit          |
|---|---------------|---------------|---|----------|------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$                       | —        | —    | $\pm 10$ | $\mu\text{A}$ |
| Gate-source breakdown voltage                   |               | $V_{(BR)GSS}$ | $I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$                      | $\pm 30$ | —    | —        | V             |
| Drain cut-off current                           |               | $I_{DSS}$     | $V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}$                          | —        | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$                             | 900      | —    | —        | V             |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$                             | 2.0      | —    | 4.0      | V             |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 4\text{ A}$                              | —        | 1.05 | 1.25     | $\Omega$      |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 15\text{ V}, I_D = 4\text{ A}$                              | 3.5      | 7.0  | —        | S             |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$         | —        | 2150 | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$     |   | —        | 35   | —        |               |
| Output capacitance                              |               | $C_{oss}$     |   | —        | 220  | —        |               |
| Switching time                                  | Rise time     | $t_r$         |   | —        | 25   | —        | ns            |
|   | Turn-on time  | $t_{on}$      |   | —        | 60   | —        |               |
|   | Fall time     | $t_f$         |   | —        | 25   | —        |               |
|   | Turn-off time | $t_{off}$     |   | —        | 120  | —        |               |
| Total gate charge (Gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$ | —        | 70   | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$      |   | —        | 37   | —        |               |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |   | —        | 33   | —        |               |

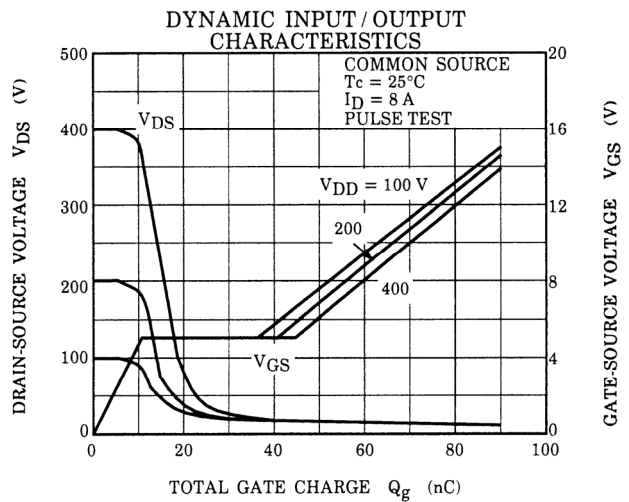
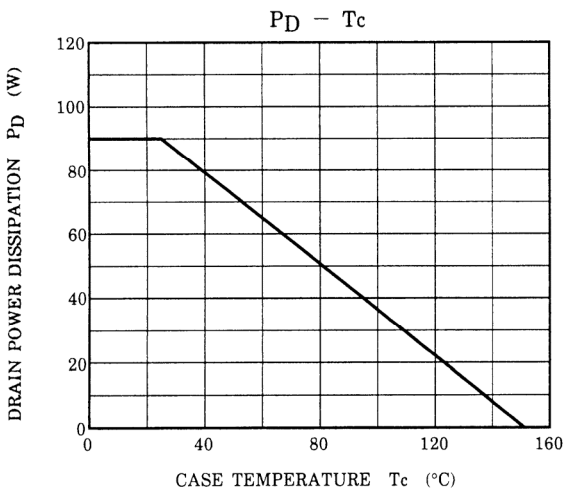
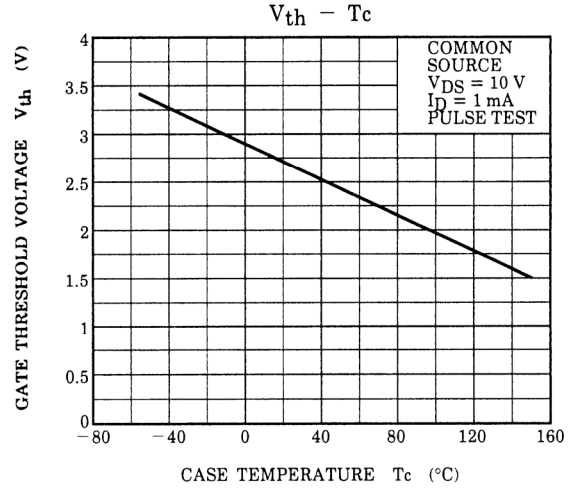
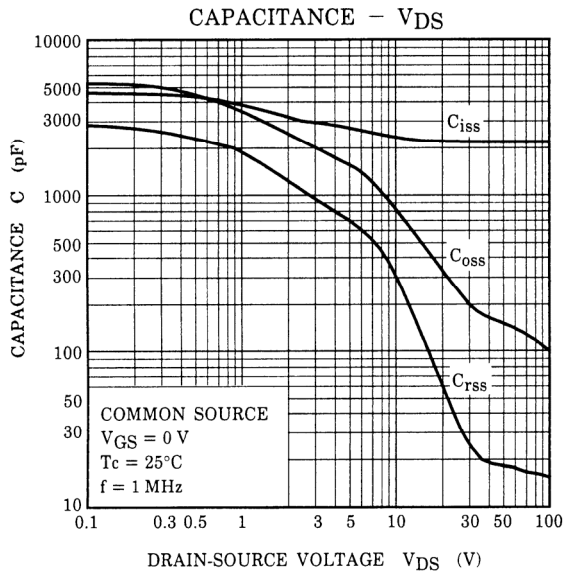
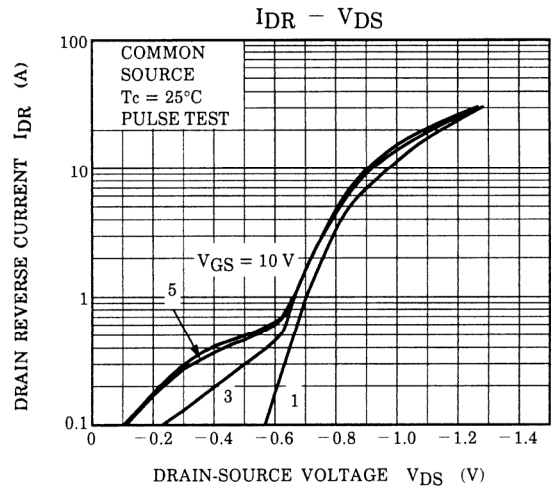
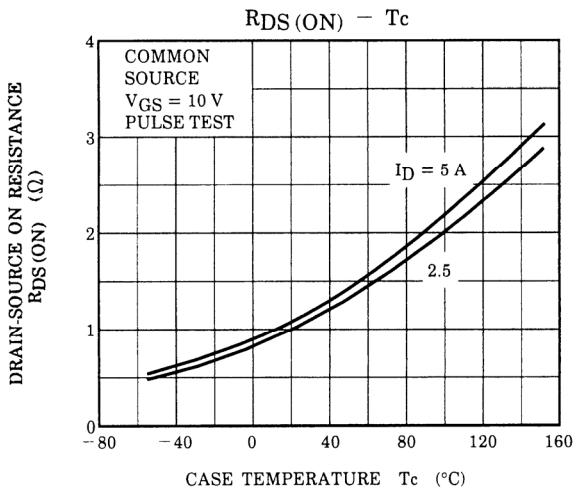
## Source-Drain Ratings and Characteristics (Ta = 25°C)

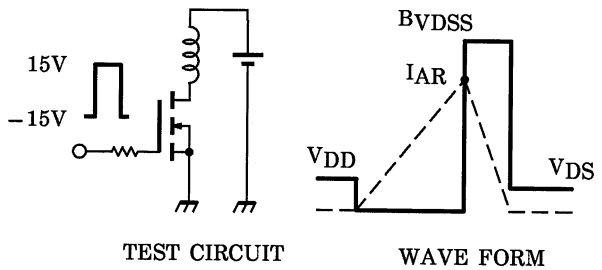
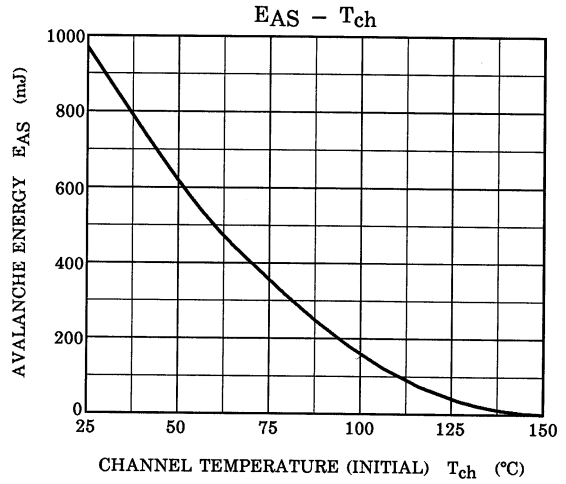
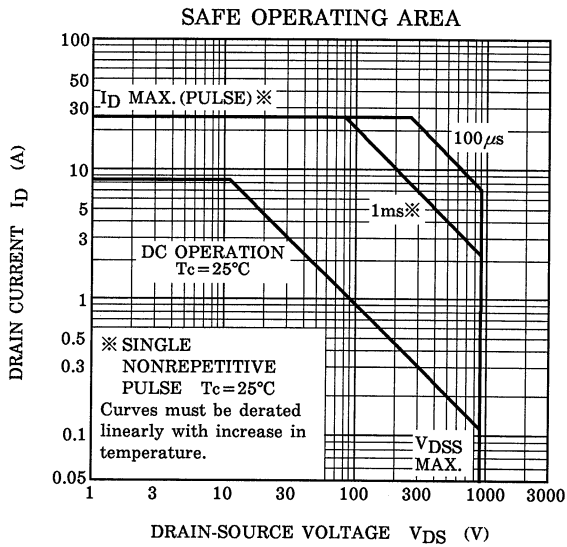
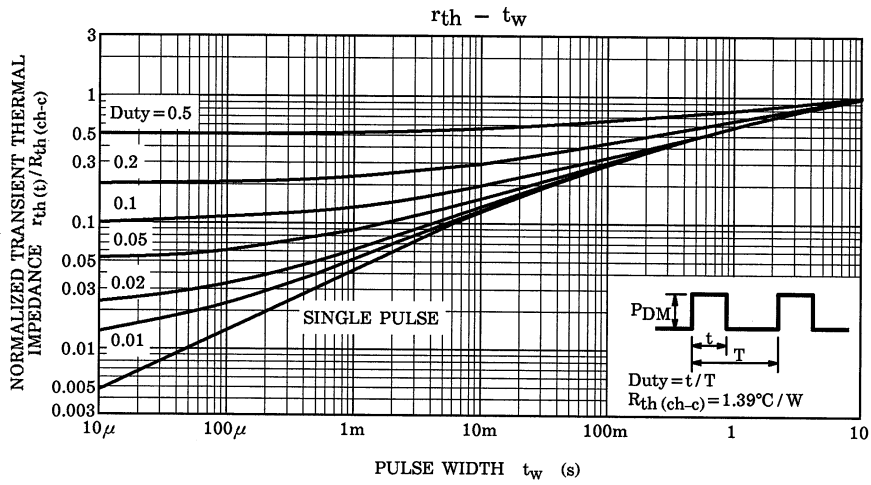
| Characteristics                           | Symbol    | Test Condition                               | Min | Typ. | Max  | Unit          |
|---|-----------|--|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —  | —   | —    | 8.5  | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —  | —   | —    | 25.5 | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 8.5\text{ A}, V_{GS} = 0\text{ V}$ | —   | —    | -1.9 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 8.5\text{ A}, V_{GS} = 0\text{ V}$ | —   | 1300 | —    | ns            |
| Reverse recovery charge                   | $Q_{rr}$  | $dI_{DR} / dt = 100\text{ A} / \mu\text{s}$  | —   | 14.5 | —    | $\mu\text{C}$ |

## Marking









$R_G = 25 \Omega$

$V_{DD} = 90 V, L = 24.5 mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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